P-Channel 60-V (D-S) MOSFET

Key Features:

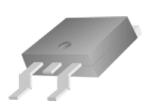
- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

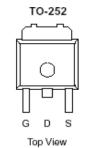
Typical Applications:

- Load Switches
- DC/DC Conversion
- Motor Drives

PRODUCT SUMMARY			
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I _D (A)	
-60	9.8 @ V _{GS} = -10V	-58	
	13 @ V _{GS} = -4.5V	-51	







ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Limit	Units		
Drain-Source Voltage			-60	V		
Gate-Source Voltage		V_{GS}	±20	V		
Continuous Drain Current a	T _C =25°C	I _D	I _D -58			
Pulsed Drain Current ^b			-240	А		
Continuous Source Current (Diode Conduction) ^a			-58	Α		
Power Dissipation ^a	T _C =25°C	P_D	50	W		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 175	°C		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Ambient ^a	$R_{\theta JA}$	40	°C/W		
Maximum Junction-to-Case	$R_{ heta JC}$	3	C/VV		

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

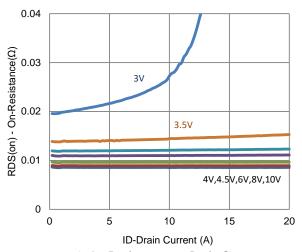
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250 \text{ uA}$	-1			V	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -48 \text{ V}, V_{GS} = 0 \text{ V}$			-1	uA	
Zero Gate Voltage Diain Current	DSS	$V_{DS} = -48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-10	uA	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-80			Α	
Drain-Source On-Resistance ^a	r	$V_{GS} = -10 \text{ V}, I_D = -29 \text{ A}$			9.8	mΩ	
Drain-Source On-Resistance	r _{DS(on)}	$V_{GS} = -4.5 \text{ V}, I_{D} = -25 \text{ A}$			13	11122	
Forward Transconductance a	g_{fs}	$V_{DS} = -15 \text{ V}, I_{D} = -29 \text{ A}$		63		S	
Diode Forward Voltage ^a	V_{SD}	I _S = -29 A, V _{GS} = 0 V		-0.86		V	
		Dynamic ^b					
Total Gate Charge	Q_g	$V_{DS} = -30 \text{ V}, V_{GS} = -4.5 \text{ V},$		66			
Gate-Source Charge	Q_{gs}	$V_{DS} = -30 \text{ V}, V_{GS} = -4.3 \text{ V},$ $I_{D} = -20 \text{ A}$		22		nC	
Gate-Drain Charge	Q_gd	1 _D = 20 //		23			
Turn-On Delay Time	$t_{d(on)}$	V 20 V D = 1.5 O		15			
Rise Time	t _r	$V_{DS} = -30 \text{ V}, R_{L} = 1.5 \Omega,$ $I_{D} = -20 \text{ A},$		21		20	
Turn-Off Delay Time	t _{d(off)}	$V_{GEN} = -10 \text{ V}, R_{GEN} = 6 \Omega$		255		ns	
Fall Time	t _f	VGEN - 10 V, NGEN 0 12		90			
Input Capacitance	C_{iss}			5884			
Output Capacitance	C_{oss}	V_{DS} = -20 V, V_{GS} = 0 V, f = 1 Mhz		475		рF	
Reverse Transfer Capacitance	C_{rss}	<u>] </u>		332			

Notes

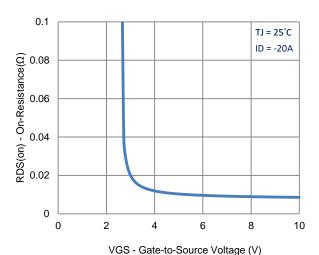
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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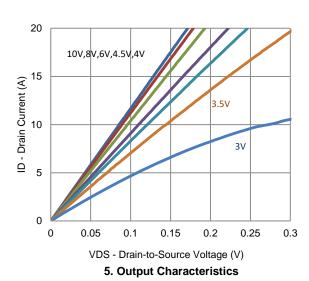
Typical Electrical Characteristics

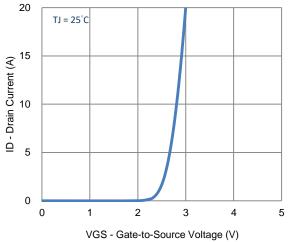


1. On-Resistance vs. Drain Current

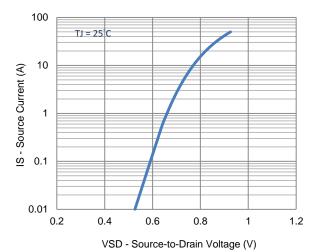


3. On-Resistance vs. Gate-to-Source Voltage

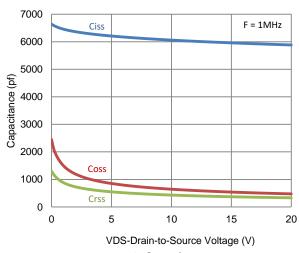




2. Transfer Characteristics

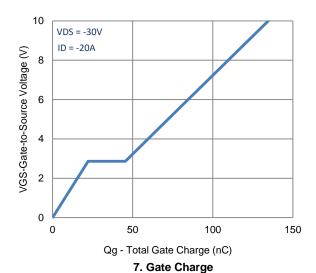


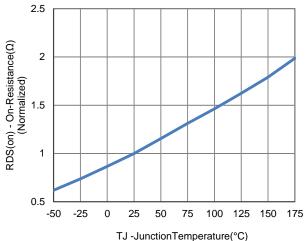
4. Drain-to-Source Forward Voltage

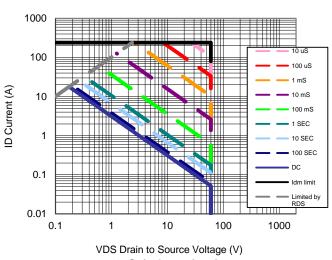


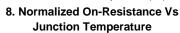
6. Capacitance

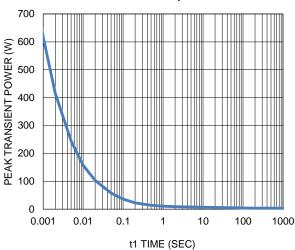
Typical Electrical Characteristics





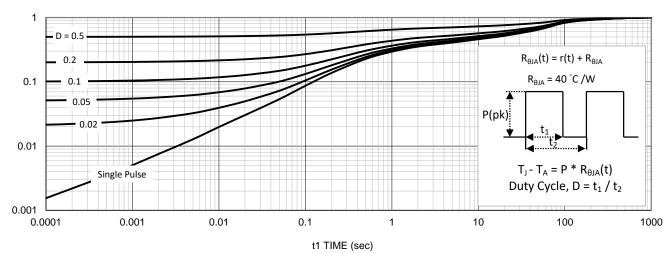






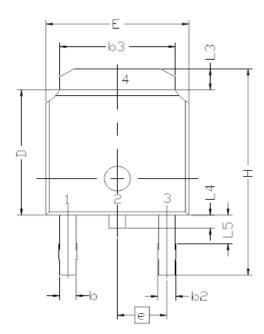
9. Safe Operating Area

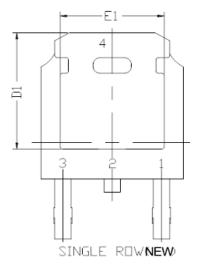
10. Single Pulse Maximum Power Dissipation

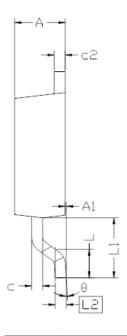


11. Normalized Thermal Transient Junction to Ambient

Package Information







CVADEL	DIMENS:	[DNAL	REQMTS		
SYMBOL	MIN	NDM	MAX		
E	6.40	6.60	6.731		
L	1.40	1.52	1.77		
L1	2.743 REF				
	0.	508 BS			
_L3	0.89		1.27		
L4	0.64		1.01		
L5					
D	6.00	6.10	6,223		
Н	9.40	10.00	10.40		
b	0.64	0.76	0.88		
b2	0.77	0.84	1.14		
b3	5,21	5.34	5.46		
е		286 BS			
Α	2,20	2,30	2.38		
A1	0		0.127		
_	0.45	0.50	0.60		
c2	0.45	0.50	0.58		
D1	5.30				
E1	4.40				
θ	0°		10°		

Note:

- 1. All Dimension Are In mm.
- Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.